

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty Docket 02DCOAI010-CA		U.S. Application No.: To be assigned	
				Applicant Naokatusu IKEGAMI			
				U.S. Filing Date: July 24, 2003		Group To be assigned	
U.S. PATENT DOCUMENTS							
Examiner Initial	AA	Document Number	Date	Name	Class	Sub-Class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
		Document Number	Pub. Date	Country	Class	Sub-Class	Translation
	AL						
	AM						
	AN						
	AO						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AR	"Deep Sub-0.1μm MOSFET's with very thin SOI layer for ultra-low power consumption", C-II vol. J81-C-II No. 3, pp 313-319 published in March, 1998 by The Institute of Electronics, Information and Communication Engineers Author : Makoto TAKAMIYA, Yuri YASUDA and Toshiro HIRAMOTO Note: English Summary is attached					
	AS	"Optimization of Series Resistance in Sub-0.2 mm SOI MOSFET's", IEEE Electron device letters, Vol. 15, No. 09 Page 363 published in September, 1994 Author : Lisa T. Su, Melanie J. Sherony, Hang Hu, James E. Chung and Dimitri A. Antonidis					
Examiner					Date Considered 12/28/05		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							